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end

42 and 44 can consist of silicon and nitrogen (or consist essentially of silicon and nitrogen), and can be, for example, Si_3N_4 . Alternatively, one of layers 42 and 44 can consist of aluminum and oxygen (or consist essentially of such materials), and the other of layers 42 and 44 can consist of silicon and nitrogen (or consist essentially of such materials). In yet another alternative embodiment, one of layers 42 and 44 can consist of silicon, nitrogen and oxygen (or consist essentially of such materials), and the other of layers 42 and 44 can consist of silicon and nitrogen (or consist essentially of such materials). An exemplary material which consists of aluminum and oxygen is Al_2O_3 --

In the Claims

Cancel claim 11.

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9. (Amended) A method of forming a transistor structure, comprising:
forming a transistor gate over a substrate, the transistor gate comprising a sidewall which comprises electrically conductive material;
forming an electrically insulative material along the electrically conductive material of the transistor gate sidewall; the electrically insulative material comprising at least two separate layers; the at least two layers having different chemical compositions from one another; a first of the at least two layers comprising at least one of $\text{Si}_x\text{O}_y\text{N}_z$ or Al_pO_q , wherein p, q, x, y and z are greater

than 0 and less than 10; a second of the at least two layers consisting essentially of silicon and nitrogen; and

anisotropically etching the electrically insulative material to form a spacer along the transistor gate sidewall; the anisotropically etching comprising etching both of the first and second of the at least two layers; and

wherein the first of the at least two layers is between the second of the at least two layers and the transistor gate sidewall.

20. (amended) The method of claim 19 wherein the electrically insulative material comprises two different layers that are against one another, one of the two layers consisting of silicon nitride, and the other of the two layers consisting of either the $\text{Si}_x\text{O}_y\text{N}_z$ or the Al_2O_3 .